

NCE15TD120LT

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1200V, 15A, Trench FS II Fast IGBT

General Description:

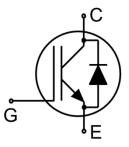
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1200V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology offering
- Very low V_{CE(sat)}
- Positive temperature coefficient in V_{CE(sat)}
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Inductive Cooking
- Soft Switching Applications



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE15TD120LT	TO-247	NCE15TD120LT



TO-247

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
Vces	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	±30	V
I-	Collector Current	30	A
lc	Collector Current @Tc = 100 °C	15	A
I _{Cpuls}	Pulsed Collector Current, tp limited by T _{jmax}	45	A
-	turn off safe operating area, V _{CE} =1350V, Tj=150°C	45	A
lF	Diode Continuous Forward Current @Tc = 100 °C	15	A
I _{FM}	Diode Maximum Forward Current	45	A
P _D	Power Dissipation @ T _C = 25°C	300	W
	Power Dissipation @T _C = 100 °C	150	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	°C
TL	Maximum Temperature for Soldering	260	°C

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Thermal Characteristic

Symbol	Parameter	Value	Units
Rejc	Thermal Resistance, Junction to case for IGBT	0.50	°C/W
Rejc	Thermal Resistance, Junction to case for Diode	0.86	°C/W
R _θ ЈА	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions -	Value			11	
			Min.	Тур.	Max.	Units	
Static Chara	cteristics	·					
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V,I _{CE} =1mA	1200			V	
Ices	Collector-Emitter Leakage Current	V _{GE} =0V,V _{CE} =1350V			5	uA	
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30V,V _{CE} =0V			200	nA	
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30V,V _{CE} =0V			200	nA	
\/	Collector-Emitter Saturation Voltage	V _{GE} =15V,I _C =15A, Tj=25°C		1.50	1.75	V	
$V_{CE(sat)}$		V _{GE} =15V,I _C =15A, Tj=150°C		1.75		V	
$V_{\text{GE(th)}}$	Gate Threshold Voltage	I _C =1mA, V _{CE} =V _{GE}	5.0		6.5	V	
Dynamic Ch	aracteristics						
Cies	Input Capacitance	V 00VVV 0V		1430		pF	
Coes	Output Capacitance	$V_{CE}=30V, V_{GE}=0V,$ f=1MHz		35			
Cres	Reverse Transfer Capacitance	I=IIVID2		25			
Qg	Total Gate Charge			90		nC	
Qge	Gate to Emitter Charge	Vcc=600V, Ic=15A V _{GE} =15V		11		nC	
Qgc	Gate to Collector Charge	VGL=10V		58		nC	
Switching Cl	naracteristics	·					
t _{d(ON)}	Turn-on Delay Time			19			
t _r	Rise Time			17		ns	
t _{d(OFF)}	Turn-Off Delay Time	Vce=600V,Ic=15A		170			
t _f	Fall Time	$V_{GE}=0/15V$, $R_g=8\Omega$		18			
Eon	Turn-On Switching Loss	Inductive Load		0.9			
E _{off}	Turn-Off Switching Loss			0.6		mJ	
Ets	Total Switching Loss			1.5			

Electrical Characteristics of the Diode (T_C= 25°C unless otherwise specified):

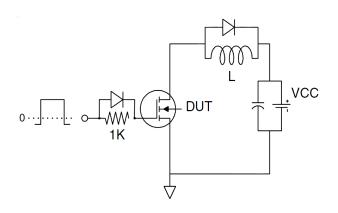
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Тур.	Max.	Ullits
V _{FM}	Diode Forward Voltage	I _F =7.5A		2.2	3.0	V
Trr	Reverse Recovery Time	I _F =7.5A, di/dt=200A/us		120		ns
I _{RRM}	Diode Peak Reverse Recovery Current			12		Α
Qrr	Reverse Recovery Charge			0.72		uC
Pulse width t _{tp} ≤380μs,δ≤2%						



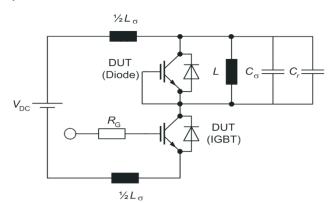
NCE15TD120LT

Test Circuit

1) Gate Charge Test Circuit

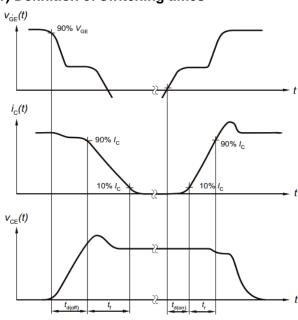


2) Switch Time Test Circuit

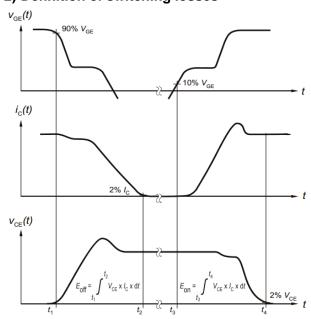


Switching characteristics

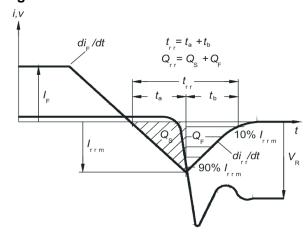
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



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Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

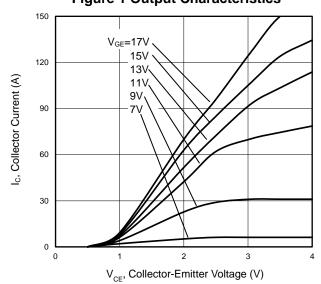


Figure 3 V_{CE(sat)} vs. Case Temperature

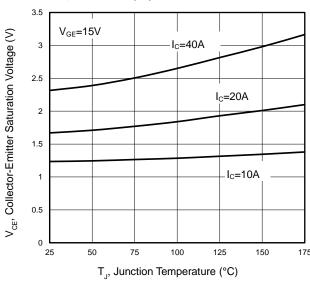


Figure 5 Capacitance Characteristics

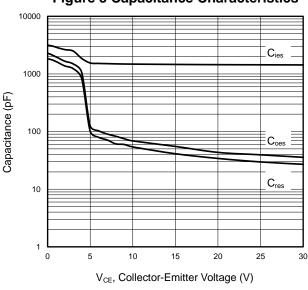


Figure 2 Transfer Characteristics

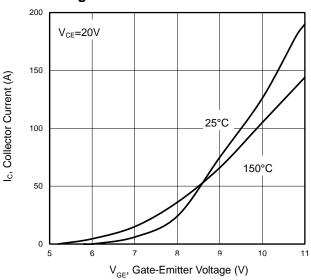


Figure 4 Saturation Voltage vs. V_{GE}

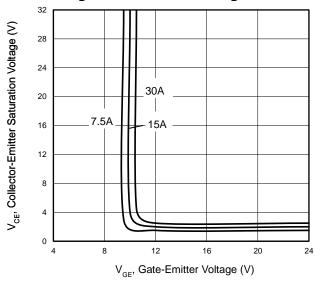
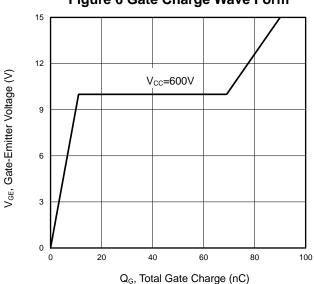


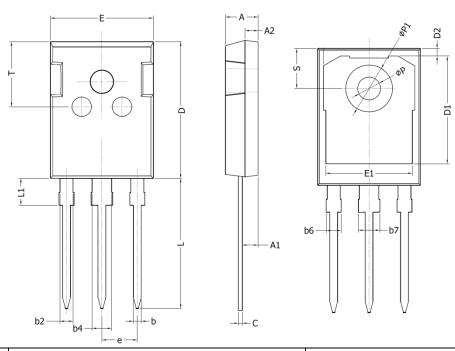
Figure 6 Gate Charge Wave Form



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TO-247-3L Package Information



Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.90	5.10	0.193	0.201	
A1	2.31	2.51	0.091	0.099	
A2	1.9	2.1	0.075	0.083	
b	1.16	1.26	0.046	0.050	
b2	1.96	2.06	0.077	0.081	
b4	2.96	3.06	0.117	0.120	
b6	-	2.25	-	0.089	
b7	-	3.25	-	0.128	
С	0.59	0.66	0.023	0.026	
D	20.90	21.10	0.823	0.831	
D1	16.25	16.85	0.640	0.663	
D2	1.05	1.35	0.041	0.053	
E	15.70	15.90	0.618	0.626	
E1	13.10	13.50	0.516	0.531	
е	5.436	BSC	0.214 BS	С	
L	19.80	20.10	0.780	0.791	
L1	-	4.30	-	0.169	
Р	3.40	3.60	0.134	0.142	
P1	7.00	7.40	0.276	0.291	
S	6.05	6.25	0.238	0.246	
Т	9.80	10.20	0.386	0.402	



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